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Cofc

PTO/SB/17 (12-04v2)
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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
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Effective on 12/08/2004.
Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).

FEE TRANSMITTAL For FY 2005

☐ Applicant claims small entity status. See 37 CFR 1.27

TOTAL AMOUNT OF PAYMENT (\$) 100.00

Complete if Known

Application Number Patent#: 6,838,307
Filing Date Issued: January 4, 2005
First Named Inventor Terry L. Gilton
Examiner Name H. M. Lee
Art Unit 2823
Attorney Docket No. M4065.1006/P1006-A

Certificate
OCT 07 2009
of Correction

METHOD OF PAYMENT (check all that apply)

☐ Check ☒ Credit Card ☐ Money Order ☐ None ☐ Other (please identify):
☒ Deposit Account Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP

For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)

☐ Charge fee(s) indicated below ☐ Charge fee(s) indicated below, except for the filing fee
☐ Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17 ☒ Credit any overpayments

FEE CALCULATION

1. BASIC FILING, SEARCH, AND EXAMINATION FEES

Application Type	FILING FEES		SEARCH FEES		EXAMINATION FEES		Fees Paid (\$)
	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	

2. EXCESS CLAIM FEES

Fee Description	Fee (\$)	Small Entity Fee (\$)
Each claim over 20 (including Reissues)	50	25
Each independent claim over 3 (including Reissues)	200	100
Multiple dependent claims	360	180

Total Claims Extra Claims Fee (\$) Fee Paid (\$)
- = x =

Multiple Dependent Claims
Fee (\$) Fee Paid (\$)

Indep. Claims Extra Claims Fee (\$) Fee Paid (\$)
- = x =

3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

Total Sheets Extra Sheets Number of each additional 50 or fraction thereof Fee (\$) Fee Paid (\$)
- 100 = /50 (round up to a whole number) x =

4. OTHER FEE(S)

Non-English Specification, \$130 fee (no small entity discount)

Other (e.g., late filing surcharge): 1811 Certificate of correction

Fees Paid (\$)
100.00

SUBMITTED BY			
Signature		Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 828-2232
		Date	September 30, 2005

OCT 12 2005



Docket No.: M4065.1006/P1006-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Terry L. Gilton

Patent No.: 6,838,307

Issued: January 4, 2005

For: PROGRAMMABLE CONDUCTOR MEMORY
CELL STRUCTURE AND METHOD
THEREFOR

**REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.323**

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the U.S. Patent Documents portion of References Cited the following 108 patent documents were omitted and should be included:

DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT
US 6,673,648	1/2004	Lowrey
US 2004/0035401	2/2004	Ramachandran et al.
US 2003/0212724	11/2003	Ovshinsky et al.
US 2003/0048744	3/2003	Ovshinsky et al.
US 2003/0212725	11/2003	Ovshinsky et al.
US RE 37,259E	7/2001	Ovshinsky
US 3,271,591	9/1966	Ovshinsky

DSMDB.1978822.1

10/03/2005 SFELEKE1 00000094 6838307

01 FC:1811

100.00 OP

OCT 12 2005

US 3,961,314	6/1976	Klose et al.
US 3,966,317	6/1976	Wacks et al.
US 3,983,542	11/1976	Ovshinsky
US 3,988,720	10/1976	Ovshinsky
US 4,177,474	12/1979	Ovshinsky
US 4,267,261	5/1981	Hallman et al.
US 4,597,162	7/1986	Johnson et al.
US 4,608,296	8/1986	Keem et al.
US 4,637,895	1/1987	Ovshinsky et al.
US 4,646,266	2/1987	Ovshinsky et al.
US 4,664,939	5/1987	Ovshinsky
US 4,668,968	5/1987	Ovshinsky et al.
US 4,670,763	6/1987	Ovshinsky et al.
US 4,673,957	6/1987	Ovshinsky et al.
US 4,678,679	7/1987	Ovshinsky
US 4,696,758	9/1987	Ovshinsky et al.
US 4,698,234	10/1987	Ovshinsky et al.
US 4,710,899	12/1987	Young et al.
US 4,728,406	3/1988	Banerjee et al.
US 4,737,379	4/1988	Hudgens et al.
US 4,766,471	8/1988	Ovshinsky et al.
US 4,769,338	9/1988	Ovshinsky et al.
US 4,775,425	10/1988	Guha et al.
US 4,788,594	11/1988	Ovshinsky et al.
US 4,809,044	2/1989	Pryor et al.
US 4,818,717	4/1989	Johnson et al.
US 4,843,443	6/1989	Ovshinsky et al.
US 4,845,533	7/1989	Pryor et al.
US 4,853,785	8/1989	Ovshinsky et al.
US 4,891,330	1/1990	Guha et al.
US 5,128,099	7/1992	Strand et al.
US 5,159,661	10/1992	Ovshinsky et al.
US 5,166,758	11/1992	Ovshinsky et al.
US 5,177,567	1/1993	Klersy et al.
US 5,296,716	3/1994	Ovshinsky et al.
US 5,335,219	8/1994	Ovshinsky et al.
US 5,359,205	10/1994	Ovshinsky
US 5,341,328	8/1994	Ovshinsky et al.
US 5,406,509	4/1995	Ovshinsky et al.
US 5,414,271	5/1995	Ovshinsky et al.
US 5,534,711	7/1996	Ovshinsky et al.
US 5,534,712	7/1996	Ovshinsky et al.
US 5,536,947	7/1996	Klersy et al.

US 5,543,737	8/1996	Ovshinsky
US 5,591,501	1/1997	Ovshinsky et al.
US 5,596,522	1/1997	Ovshinsky et al.
US 5,687,112	11/1997	Ovshinsky
US 5,694,054	12/1997	Ovshinsky et al.
US 5,714,768	2/1998	Ovshinsky et al.
US 5,825,046	10/1998	Czubatyj et al.
US 5,912,839	6/1999	Ovshinsky et al.
US 5,933,365	8/1999	Klersy et al.
US 6,011,757	1/2000	Ovshinsky
US 6,087,674	7/2000	Ovshinsky et al.
US 6,141,241	10/2000	Ovshinsky et al.
US 6,339,544	1/2002	Chiang et al.
US 6,404,665	6/2002	Lowery et al.
US 6,429,064	8/2002	Wicker
US 6,437,383	8/2002	Xu
US 6,462,984	10/2002	Xu et al.
US 6,480,438	11/2002	Park
US 6,487,113	11/2002	Park et al.
US 6,501,111	12/2002	Lowery
US 6,507,061	1/2003	Hudgens et al.
US 6,511,862	1/2003	Hudgens et al.
US 6,511,867	1/2003	Lowery et al.
US 6,512,241	1/2003	Lai
US 6,514,805	2/2003	Xu et al.
US 6,531,373	3/2003	Gill et al.
US 6,534,781	3/2003	Dennison
US 6,545,287	4/2003	Chiang
US 6,545,907	4/2003	Lowery et al.
US 6,555,860	4/2003	Lowery et al.
US 6,563,164	5/2003	Lowery et al.
US 6,566,700	5/2003	Xu
US 6,567,293	5/2003	Lowery et al.
US 6,569,705	5/2003	Chiang et al.
US 6,570,784	5/2003	Lowery
US 6,576,921	6/2003	Lowery
US 6,586,761	7/2003	Lowery
US 6,589,714	7/2003	Maimon et al.
US 6,590,807	7/2003	Lowery
US 6,593,176	7/2003	Dennison
US 6,597,009	7/2003	Wicker
US 6,605,527	8/2003	Dennison et al.
US 6,613,604	9/2003	Maimon et al.

US 6,621,095	9/2003	Chiang et al.
US 6,625,054	9/2003	Lowery et al.
US 6,642,102	11/2003	Xu
US 6,646,297	11/2003	Dennison
US 6,649,928	11/2003	Dennison
US 6,667,900	12/2003	Lowery et al.
US 6,671,710	12/2003	Ovshinsky et al.
US 6,673,700	1/2004	Dennison et al.
US 6,674,115	1/2004	Hudgens et al.
US 6,687,427	2/2004	Ramalingam et al.
US 6,690,026	2/2004	Peterson
US 6,696,355	2/2004	Dennison
US 6,687,153	2/2004	Lowery
US 6,707,712	3/2004	Lowery
US 6,714,954	3/2004	Ovshinsky et al.

Attached Exhibit A includes copies of PTO Forms SB/08a listing these patent documents. Each document listed has been initialed as reviewed and accepted by the Examiner on 9/15/2004.

In the Foreign Patent Documents portion of References Cited the following reference contains a typographical error by the PTO to be corrected:

“WO WO 99/28194 6/1999” should read

--WO WO 99/28914 6/1999--.

In the Other Publications portion of References Cited the following references contain typographical errors by the PTO which should be corrected:

“Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilay r electrode, Thin Solid Films 131 (1985) L61-L64.”
Should read

--Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64.--;

“Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below T_g : elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.” Should read

--Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below T_g : elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.--;

“Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.” Should read

--Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.--;

“Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in $\text{Ge}_{1-x}\text{Se}_x$ glass, Appl. Phys. Lett. 46 (1985) 543-545.” Should read

--Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in $\text{Ge}_{1-x}\text{Se}_x$ glass, Appl. Phys. Lett. 46 (1985) 543-545.--;

“McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)” Should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)--;

“Messoussi, R.; Berneda, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures ($M=\text{Ni}$), J. Mat. Chem. And Phys. 28 (1991) 253-258.” Should read

--Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures ($M=\text{Ni}$, Bi), Mat. Chem. And Phys. 28 (1991) 253-258.--;

“Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.” Should read

--Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.--;

“Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.” Should read

--Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.--;

“Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 48 B. Chem Soc. Japan, No. 12, pp. 3662-3365 (1973).” Should read

--Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 46 B, Chem. Soc. Japan, No. 12, pp. 3662-3365 (1973).--; and

“Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T_g , with average coordination number, $\langle m \rangle$, in network glasses: evidence of a threshold behavior in the slope $|dT_g/d\langle m \rangle|$ at the rigidity percolation threshold ($\langle m \rangle \times 2.4$), J. Non-Cryst. Solids 151 (1992) 149-154.” Should read

--Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T_g , with average coordination number, $\langle m \rangle$, in network glasses: evidence of a threshold behavior in the slope $|dT_g/d\langle m \rangle|$ at the rigidity percolation threshold ($\langle m \rangle \times 2.4$), J. Non-Cryst. Solids 151 (1992) 149-154.--.

In the Specification the Applicant made the following errors:

Column 2, line 51, “and” should read --an--;

Column 6, line 2, “ovelying” should read --overlying--;

Column 6, line 58, “provide” should read --provided--; and

Column 6, line 60, “contining” should read --containing--.

The errors were made both by the PTO and found in the application as filed by applicant. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such corrections. Patentee respectfully solicits the granting of the requested Certificate of Correction.

Patent No.: 6,838,307

Docket No.: M4065.1006/P1006-A

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.1006/P1006-A.

Dated: September 30, 2005

Respectfully submitted,

By 
Thomas J. D'Amico

Registration No.: 28,371

Peter McGee

Registration No.: 35,947

DICKSTEIN SHAPIRO MORIN & OSHINSKY
LLP

2101 L Street NW

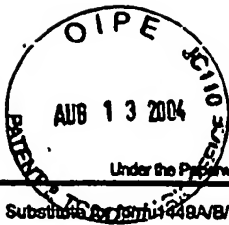
Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicant

Exhibit A

OCT 12 2005



Substitution Form 1448A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete If Known	
				Application Number	10/618,824-Conf. #5907
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A- 2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	1	of	1	Attorney Docket Number	M4065.1006/P1006-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JA	AA	US-6,673,648	01/06/2004	Lowrey	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

Kevin Ming Lu

9/15/2004



PTO/SB/08a/b (08-03)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/618,824
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2823
				Examiner Name	Hsien Ming Lee
				Attorney Docket Number	M4065.1006/P1006-A
Sheet	1	of	3		

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
Lee	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,981,314	8/1976	Klose et al.	
	H	US 3,986,317	8/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky	
	K	US 4,177,474	12/1979	Ovshinsky	
	L	US 4,267,261	5/1981	Hallman et al.	
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
	P	US 4,646,266	2/1987	Ovshinsky et al.	
	Q	US 4,664,939	5/1987	Ovshinsky	
	R	US 4,668,968	5/1987	Ovshinsky et al.	
	S	US 4,670,763	6/1987	Ovshinsky et al.	
	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Y	US 4,728,406	3/1988	Banerjee et al.	
	Z	US 4,737,379	4/1988	Hudgens et al.	
	A1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	C1	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
	E1	US 4,809,044	2/1989	Pryor et al.	
	F1	US 4,818,717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	H1	US 4,845,533	7/1989	Pryor et al.	
	I1	US 4,853,785	8/1989	Ovshinsky et al.	
	J1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,681	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992	Ovshinsky et al.	
	N1	US 5,177,587	1/1993	Klarsy et al.	
	Q1	US 5,298,716	3/1994	Ovshinsky et al.	
	P1	US 5,335,219	8/1994	Ovshinsky et al.	
	Q1	US 5,359,205	10/1994	Ovshinsky	
	R1	US 5,341,328	8/1994	Ovshinsky et al.	
Lee	S1	US 5,408,509	4/1995	Ovshinsky et al.	

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2823
				Examiner Name	Hsien Ming Lee
				Attorney Docket Number	M4065.1006/P1006-A
Sheet	2	of	3		

T1	US 5,414,271	5/1995	Ovshinsky et al.	
U1	US 5,534,711	7/1998	Ovshinsky et al.	
V1	US 5,534,712	7/1998	Ovshinsky et al.	
W1	US 5,536,947	7/1998	Klersy et al.	
X1	US 5,543,737	8/1998	Ovshinsky	
Y1	US 5,581,501	1/1997	Ovshinsky et al.	
Z1	US 5,586,522	1/1997	Ovshinsky et al.	
A2	US 5,687,112	11/1997	Ovshinsky	
B2	US 5,694,054	12/1997	Ovshinsky et al.	
C2	US 5,714,768	2/1998	Ovshinsky et al.	
D2	US 5,825,046	10/1998	Czubatyj et al.	
E2	US 5,912,839	6/1999	Ovshinsky et al.	
F2	US 5,933,365	8/1999	Klersy et al.	
G2	US 6,011,757	1/2000	Ovshinsky	
H2	US 6,087,674	7/2000	Ovshinsky et al.	
I2	US 6,141,241	10/2000	Ovshinsky et al.	
J2	US 6,339,544	1/2002	Chiang et al.	
K2	US 6,404,665	6/2002	Lowery et al.	
L2	US 6,429,064	8/2002	Wicker	
M2	US 6,437,383	8/2002	Xu	
N2	US 6,462,984	10/2002	Xu et al.	
O2	US 6,480,438	11/2002	Park	
P2	US 6,487,113	11/2002	Park et al.	
Q2	US 6,501,111	12/2002	Lowery	
R2	US 6,507,061	1/2003	Hudgens et al.	
S2	US 6,511,862	1/2003	Hudgens et al.	
T2	US 6,511,867	1/2003	Lowery et al.	
U2	US 6,512,241	1/2003	Lai	
V2	US 6,514,805	2/2003	Xu et al.	
W2	US 6,531,373	3/2003	Gill et al.	
X2	US 6,534,781	3/2003	Dennison	
Y2	US 6,545,287	4/2003	Chiang	
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A3	US 6,555,860	4/2003	Lowery et al.	
B3	US 6,563,164	5/2003	Lowery et al.	
C3	US 6,566,700	5/2003	Xu	
D3	US 6,567,293	5/2003	Lowery et al.	
E3	US 6,569,705	5/2003	Chiang et al.	
F3	US 6,570,784	5/2003	Lowery	
G3	US 6,576,921	6/2003	Lowery	
H3	US 6,586,761	7/2003	Lowery	
I3	US 6,589,714	7/2003	Malmou et al.	
J3	US 6,590,807	7/2003	Lowery	
K3	US 6,593,176	7/2003	Dennison	
L3	US 6,597,009	7/2003	Wicker	
M3	US 6,605,527	8/2003	Dennison et al.	
N3	US 6,613,604	9/2003	Malmou et al.	
O3	US 6,621,095	9/2003	Chiang et al.	
P3	US 6,625,054	9/2003	Lowery et al.	
Q3	US 6,642,102	11/2003	Xu	

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Substitute for form 1448A/B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2823
				Examiner Name	Hsien Ming Lee
Sheet	3	of	3	Attorney Docket Number	M4065.1006/P1006-A

<i>La</i>	R3	US 6,646,297	11/2003	Dennison	
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,667,800	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,700	1/2004	Dennison et al.	
	W3	US 6,674,115	1/2004	Hudgens et al.	
	X3	US 6,687,427	2/2004	Ramalingam et al.	
	Y3	US 6,690,026	2/2004	Peterson	
	Z3	US 6,696,355	2/2004	Dennison	
	A4	US 6,687,153	2/2004	Lowery	
	B4	US 6,707,712	3/2004	Lowery	
<i>La</i>	C4	US 6,714,954	3/2004	Ovshinsky et al.	

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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	To
		Country Code ² -Number ³ -Kind Code ⁴ (if known)					

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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Hsien Ming Lee

9/15/2004

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 5

PATENT NO. : 6,838,307
APPLICATION NO. : 10/618,824
ISSUE DATE : January 4, 2005
INVENTOR(S) : Terry L. Gilton

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the U.S. Patent Documents portion of References Cited the following 108 patents were omitted and should be included:

DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT
US 6,673,648	1/2004	Lowrey
US 2004/0035401	2/2004	Ramachandran et al.
US 2003/0212724	11/2003	Ovshinsky et al.
US 2003/0048744	3/2003	Ovshinsky et al.
US 2003/0212725	11/2003	Ovshinsky et al.
US RE 37,259E	7/2001	Ovshinsky
US 3,271,591	9/1966	Ovshinsky
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US 4,177,474	12/1979	Ovshinsky
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US 4,608,296	8/1986	Keem et al.
US 4,637,895	1/1987	Ovshinsky et al.
US 4,646,266	2/1987	Ovshinsky et al.

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US 4,664,939	5/1987	Ovshinsky
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US 6,605,527	8/2003	Dennison et al.
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US 6,621,095	9/2003	Chiang et al.
US 6,625,054	9/2003	Lowery et al.
US 6,642,102	11/2003	Xu
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US 6,671,710	12/2003	Ovshinsky et al.
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US 6,690,026	2/2004	Peterson
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US 6,687,153	2/2004	Lowery
US 6,707,712	3/2004	Lowery
US 6,714,954	3/2004	Ovshinsky et al.

In the Foreign Patent Documents portion of References Cited:

"WO WO 99/28194 6/1999" should read
 --WO WO 99/28914 6/1999--.

In the Other Publications portion of References Cited these typographical errors need corrections:

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Thomas J. D'Amico
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"Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilay r electrode, Thin Solid Films 131 (1985) L61-L64." Should read

--Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin Solid Films 131 (1985) L61-L64.--;

"Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide galss s glass s below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269." Should read

--Guin, J.-P.; Roux, I. T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, L.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.--;

"Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G /Se glasses: clust ring f Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142." Should read

--Iyetomi, H.; Vashista, P.; Kalia, R.K., Incipient phase separation in Ag/G/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.--;

"Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. L tt. 46 (1985) 543-545." Should read

--Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.--;

"McHardy et al., The dissolution of metals in am rphous chalcogenid s and the eff cts o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f" Should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)--;

"Messoussi, R.; Berneda, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=N), i.Bi Mat. Chem. And Phys. 28 (1991) 253-258." Should read

--Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258.--;

"Popescu, C.; Croitoru, N., The contribution of the lateral thermal Instability to th switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537." Should read

--Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.--;

"Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphou s lenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73." Should read

--Popov, A.I.; Geller, I.K.H.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.--;

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"Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 48 B. Chem Soc. Japan, No. 12, pp. 3662-3365 (1973)." Should read

--Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 46 B, Chem. Soc. Japan, No. 12, pp. 3662-3365 (1973).--; and

"Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T_g , with average coordination number, $\langle m \rangle$, in network glasses: evidence of a threshold behavior in the [slope $dT_g/d\langle m \rangle$] at the rigidity percolation threshold ($\langle m \rangle \times 2.4$), J. Non-Cryst. Solids 151 (1992) 149-154." Should read

--Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T_g , with average coordination number, $\langle m \rangle$, in network glasses: evidence of a threshold behavior in the slope $|dT_g/d\langle m \rangle|$ at the rigidity percolation threshold ($\langle m \rangle \times 2.4$), J. Non-Cryst. Solids 151 (1992) 149-154.--.

In the Specification the Applicant made the following errors:

Column 2, line 51, "and" should read --an--;

Column 6, line 2, "ovelying" should read --overlying--;

Column 6, line 58, "provide" should read --provided--; and

Column 6, line 60, "contining" should read --containing--.

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